

**Amendments to the Specification:**

Please amend the specification as follows:

Please replace paragraph number [0034] with the following rewritten paragraph:

[Fig. 1] Fig. 1 is a diagram showing a sectional structure of a green light emitting OLED.

[Fig. 2] Fig. 2 is a graph showing the time dependence of luminous intensities of OLEDs.

[Fig. 3] Fig. 3 is a graph showing the mean free paths of neutral gas atoms.

[Fig. 4] Fig. 4 is a graph showing the time dependence of organic compound amounts adsorbed on the surfaces of substrates left standing in a depressurizing apparatus and a clean room.

[Fig. 5] Fig. 5 is a graph showing the storage pressure dependence of organic compound adhered to the surfaces of wafers.

[Fig. 6] Fig. 6 is a graph showing the chamber-fed N<sub>2</sub> gas flow rate dependence of adsorption organic amounts on the surfaces of substrates at a storage pressure of 3 Torr.

[Fig. 7] Fig. 7 is a graph showing the time dependence of adsorption organic compound amount on the surface of a substrate in a vacuum state of  $7.5 \times 10^{-8}$  Torr.

[Fig. 8] Fig. 8 is a graph showing the temperature dependence of ion currents of mass numbers 28, 43, and 57 measured by a quadrupole mass spectrometer in a chamber at a pressure of  $7.5 \times 10^{-8}$  Torr where a SiO<sub>2</sub> coated silicon substrate adhered with eicosane (C<sub>20</sub>H<sub>42</sub>) is located.

[Fig. 9] Fig. 9 is a graph showing the pressure dependence of ion currents of mass numbers 28, 43, and 57 by the use of a quadrupole mass spectrometer when the pressure in a chamber is changed by a N<sub>2</sub> gas while maintaining the temperature constant.

[Fig. 10] Fig. 10 is a graph showing the temperature dependence of ion currents, by the use of a quadrupole mass spectrometer, of mass numbers 43 and 57 being dissociated molecules of eicosane (C<sub>20</sub>H<sub>42</sub>) in an atmospheric vacuum atmosphere of  $7.5 \times 10^{-8}$  Torr.

[Fig. 11] Fig. 11 is a graph showing the time dependence of substrate surface adsorption amounts of C<sub>20</sub>H<sub>42</sub> molecules when the pressure in a chamber is changed to 90 Torr, 10 Torr, and 3 Torr.

[Fig. 12A] Fig. 12A is a graph showing characteristics of  $C_{20}H_{42}$  molecules and is the graph showing surface equilibrium adsorption amounts of substrate surface adsorption.

[Fig. 12B] Fig. 12B is a graph showing characteristics of  $C_{20}H_{42}$  molecules and is the graph showing the pressure dependence of adsorption time constant.

[Fig. 13] Fig. 13 is a graph showing the pressure dependence of substrate surface adsorption amounts of  $C_{20}H_{42}$  molecules when the exposure time of the surfaces of substrates is changed to seven kinds from 1 minute to 400 minutes.

[Fig. 14A] Fig. 14A is a graph showing the molecular weight dependence of adsorption amount in the case of straight-chain hydrocarbon adsorbed on the substrate surface at room temperature under the atmospheric pressure.

[Fig. 14B] Fig. 14B is a graph showing the molecular weight dependence of adsorption amount in the case of phthalate ester adsorbed on the substrate surface at room temperature under the atmospheric pressure.

[Fig. 14C] Fig. 14C is a graph showing the molecular weight dependence of adsorption amount in the case of cyclic siloxane adsorbed on the substrate surface at room temperature under the atmospheric pressure.

[Fig. 15] Fig. 15 is a schematic diagram showing the structure of a gas exhaust system of a reduced-pressure deposition apparatus.

[Fig. 16] Fig. 16 is a graph showing the relationship between chamber pressure and gas flow rate given to a chamber.

[Fig. 17A] Fig. 17A is a diagram showing a molecular structure of Alq3.

[Fig. 17B] Fig. 17B is a diagram showing a molecular structure of NPD.

[Fig. 18] Fig. 18 is a diagram showing a schematic structure of an experimentation system for evaluating dissociation of Alq3 molecules.

[Fig. 19] Fig. 19 is a graph showing FT-IR absorption spectra of evaporated Alq3 at (a) and FT-IR absorption spectra of solid Alq3 at (b), respectively.

[Fig. 20] Fig. 20 is a graph showing FT-IR absorption spectra of water molecules ( $H_2O$ ) and a  $CO_2$  gas.

[Fig. 21] Fig. 21 is a graph showing IR spectra identification of Alq3.

[Fig. 22] Fig. 22 is a graph showing the temperature dependence of respective Alq3 peaks.

[Fig. 23] Fig. 23 is a graph showing comparison between infrared absorption spectra of NPD in a gas phase at (a) and in a solid phase at (b).

[Fig. 24] Fig. 24 is a graph showing infrared absorption spectra of NPD molecules.

[Fig. 25] Fig. 25 is a graph showing the temperature dependence of respective NPD peaks in the evaporation dish.

[Fig. 26] Fig. 26 is a sectional view showing a schematic structure of an organic film-forming apparatus.

[Fig. 27] Fig. 27 is a graph for explaining Cu elution amounts in various waters.

[Fig. 28] Fig. 28 is a diagram for explaining the structure of a temperature control cooling water circulation system.

[Fig. 29] Fig. 29 is a diagram for explaining the shape of a cooling pipe.

[Fig. 30] Fig. 30 is a diagram for explaining the structure of a temperature control cooling water circulation system.

[Fig. 31] Fig. 31 is a diagram showing a section of an organic compound molecule ejection apparatus portion.

[Fig. 32] Fig. 32 is a diagram showing the structure of a substrate upward type organic film-forming apparatus.

[Fig. 33] Fig. 33 is a diagram showing the structure of a substrate sideward type organic film-forming apparatus.

[Fig. 34] Fig. 34 is a diagram showing the structure of an organic film-forming apparatus having a Xe or Kr gas recovery circulation system.

[Fig. 35] Fig. 35 is a diagram showing the structure of a Kr circulation supply apparatus.

[Fig. 36] Fig. 36 is a diagram showing the structure of a Xe circulation supply apparatus.

[Fig. 37] Fig. 37 is a diagram showing the structure of an Ar/Kr circulation supply apparatus.

[Fig. 38] Fig. 38 is a diagram showing the structure of an Ar/Xe circulation supply apparatus.

[Fig. 39A] Fig. 39A is a sectional view showing the structure of a gas levitation transfer apparatus.

[Fig. 39B] Fig. 39B is a perspective view showing the structure of the gas levitation transfer apparatus.

[Fig. 40] Fig. 40 is an exemplary diagram for schematically explaining a section of a film-forming apparatus.

[Fig. 41] Fig. 41 is an exemplary diagram of schematically explaining a section of a film-forming apparatus according to a modification of the embodiment of Fig. 40.

Please replace paragraph number [0104] with the following rewritten paragraph:

A film-forming apparatus in Embodiment 4 of this invention will be described with reference to Fig. 40. Fig. 40 is a sectional view showing one example of a deposition apparatus of this Embodiment 4, wherein the apparatus mainly comprises a container forming a process chamber 125 adapted to carry out a film-forming process, a substrate introduction chamber 123 coupled to the process chamber 125 through a gate valve 124 serving as a partition for the depressurizing chamber and maintaining air-tightness of the process chamber 125, so as to carry in and out a substrate 131, a substrate introduction door 121 coupled to the substrate introduction chamber 123, a substrate holder 132 adapted to hold the substrate 131 in the container, primary pumps 127 coupled to the depressurizing chamber and the substrate introduction chamber 123 through pump gate valves 126, respectively, secondary pumps 130 coupled to exhaust sides of the primary pumps 127, pump purge gas introduction mechanisms 128 and 129 each located between the primary pump 127 and the secondary pump 130 for suppressing back diffusion of impurities from the secondary pump 130, and film-forming material supply means 135 coupled to the container for supplying a film-forming material 134 or a film-forming material precursor, and further comprises substrate placing means provided in the depressurizing chamber for placing the substrate 131 to be deposited with the film-forming material, film-forming material ejection means located so as to face the substrate 131 for ejecting the film-forming material 134 or the film-forming material precursor, supplied from the film-forming material supply means 135, toward the substrate surface, and gaskets 122 provided at connecting portions of the respective members for maintaining air-tightness to the exterior. Fig. 41 illustrates a modification of the embodiment of Fig. 40, where the film-forming material supply means 135 is outside the process chamber 125.